Ordering number:EN1594B

NPN Triple Diffused Planar Silicon Transistor

2SC3460

800V/6A Switching Regulator Applications

Features

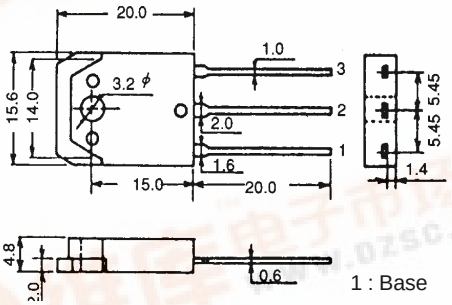
- High breakdown voltage and high reliability.
- Fast switching speed (t_f : 0.1μs typ).
- Wide ASO.
- Adoption of MBIT process.

Package Dimensions

unit:mm

2022A

[2SC3460]



1 : Base
2 : Collector
3 : Emitter
SANYO : TO-3PB

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		1100	V
Collector-to-Emitter Voltage	V_{CEO}		800	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		6	A
Collector Current (Pulse)	I_{CP}	PW≤300μs, Duty Cycle≤10%	20	A
Base Current	I_B		3	A
Collector Dissipation	P_C	Tc=25˚C	100	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=800V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC Current Gain	$h_{FE}1$	V_{CE}=5V, I_C=0.4A	10*		40*	
	$h_{FE}2$	V_{CE}=5V, I_C=2A	8			
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=0.4A		15		MHz
Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz		120		pF

* : The $h_{FE}1$ of the 2SC3460 is classified as follows. When specifying the $h_{FE}1$ rank, specify two ranks or more in principle.

10	K	20	15	L	30	20	M	40

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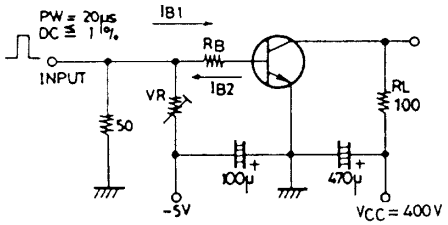
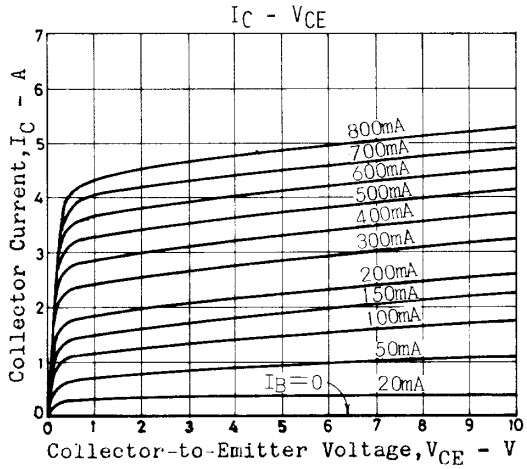
2SC3460

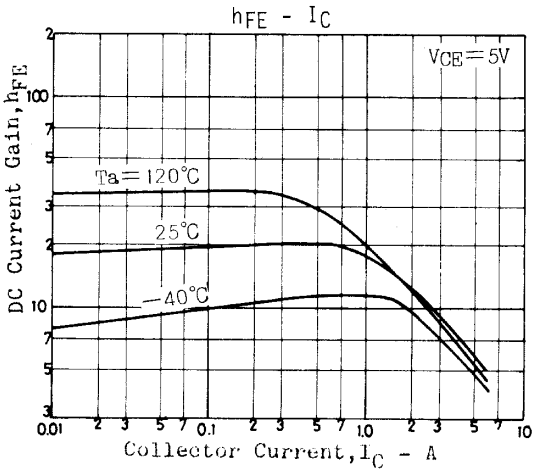
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=3A, I_B=0.6A			2.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=3A, I_B=0.6A			1.5	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	1100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=5mA, R_{BE}=∞	800			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	7			V
Collector-to-Emitter Sustain Voltage	$V_{CEX(sus)}$	I_C=3A, I_{B1}=–I_{B2}=0.6A, L=1mH, clamped	800			V
Turn-ON Time	t_{on}	V_{CC}=400V, 5I_{B1}=–2.5I_{B2}=I_C=4A, R_L=100Ω			0.5	μs
Storage Time	t_{stg}	V_{CC}=400V, 5I_{B1}=–2.5I_{B2}=I_C=4A, R_L=100Ω			3.0	μs
Fall Time	t_f	V_{CC}=400V, 5I_{B1}=–2.5I_{B2}=I_C=4A, R_L=100Ω			0.3	μs

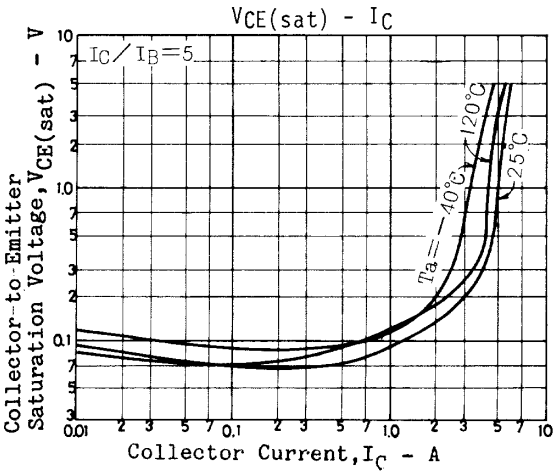
Switching Time Test Circuit

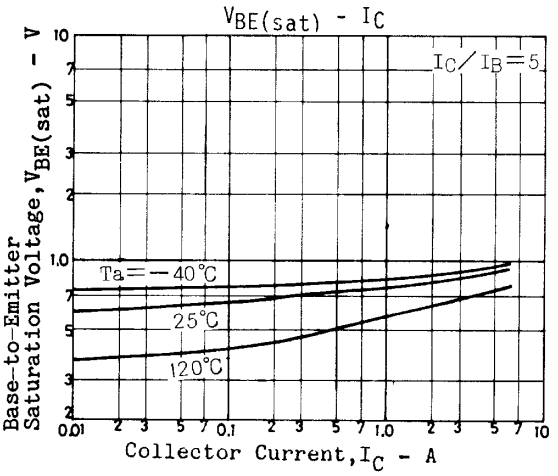


Unit (resistance : Ω, capacitance : F)

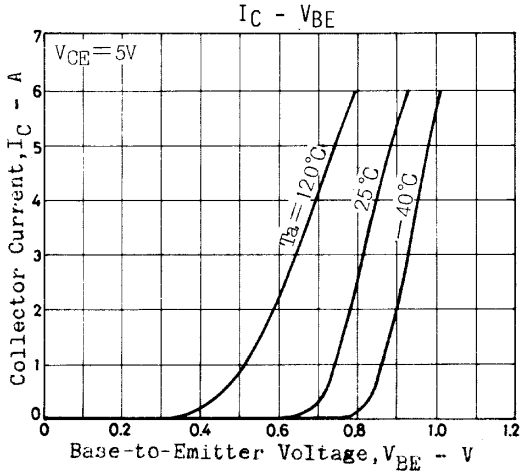




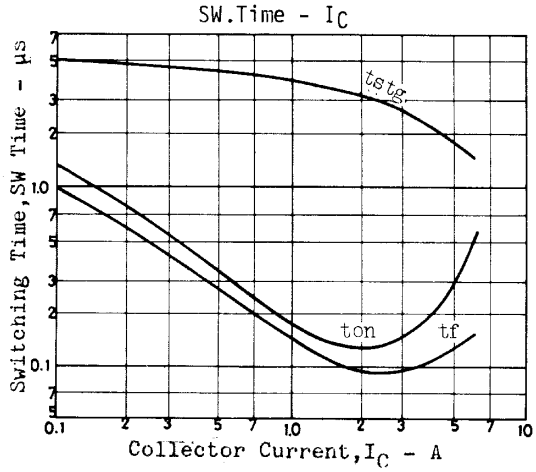




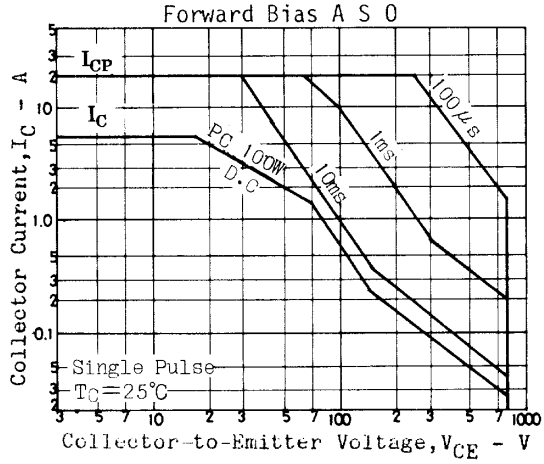
I_C - V_{BE}



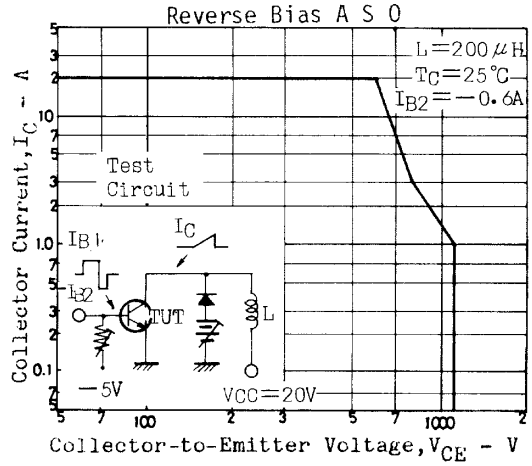
SW.Time - I_C



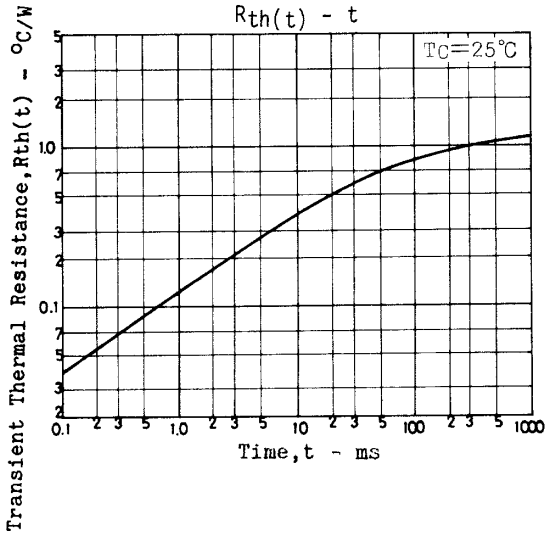
Forward Bias A S O



Reverse Bias A S O



Rth(t) - t



P_C - Tc